WHAT IS CLAIMED IS:

[CLAIM 1]

A method for forming a Schottky contact semiconductor device, comprising:

providing an evaporation chamber having therein: a first metal source, a second metal source; and a semiconductor having mask over a surface of the semiconductor, such mask having a window therein to expose a portion of the surface of the semiconductor;

evaporating a portion of a first metal from the first metal source and depositing the evaporated first metal onto the mask and onto the exposed portion of the surface of the semiconductor forming a Schottky contact between the portion of the first metal and the exposed portion of the semiconductor to form a first metal layer;

evaporating a portion of a second metal from the second metal source and depositing the evaporated second metal over the deposited first metal to form a second metal layer over the first metal layer;

evaporating a portion of the first metal from the first metal source and depositing the evaporated first metal over the deposited second metal to form a third metal layer over the second metal layer;

evaporating a portion of the second metal from the second metal source and depositing the evaporated second metal over the deposited first metal of the third metal layer to form a fourth metal layer over the third metal layer.

[CLAIM 2]

The method recited in claim 1 wherein the evaporation chamber is provided with a third metal source and the method includes: evaporating a third metal from the third metal source onto the second metal of the fourth metal layer.

[CLAIM 3]

The method recited in claim 1 including: evaporating a portion of the first metal from the first metal source and depositing the evaporated first metal over the deposited second metal to form a fifth metal layer over the fourth metal layer; and

evaporating a portion of the second metal from the second metal source and depositing the evaporated second metal over the deposited first metal of the fifth metal layer to form a sixth metal layer over the fifth metal layer.

[CLAIM 4]

The method recited in claim 3 wherein the evaporation chamber is provided with a third metal source and the method includes: evaporating a third metal from the third metal source onto the second metal of the sixth metal layer

[CLAIM 5]

The method recited in claim 4 wherein the first metal is nickel; the second metal is platinum; and the third metal is gold.